# **Triacs**Silicon Bidirectional Thyristors

Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

#### **Features**

- Blocking Voltage to 800 V
- On-State Current Rating of 8 A RMS at 80°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dV/dt 2000 V/μs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating dI/dt 1.5 A/ms minimum at 125°C
- Internally Isolated (2500 V<sub>RMS</sub>)
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS (T<sub>.1</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (T <sub>J</sub> = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	$V_{DRM,} \ V_{RRM}$		V
BTA08-600BW3G BTA08-800BW3G		600 800	
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T <sub>C</sub> = 80°C)	I <sub>T(RMS)</sub>	8.0	Α
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>C</sub> = 25°C)	I <sub>TSM</sub>	90	Α
Circuit Fusing Consideration (t = 8.3 ms)	l <sup>2</sup> t	36	A <sup>2</sup> sec
Non-Repetitive Surge Peak Off-State Voltage (T <sub>J</sub> = 25°C, t = 10ms)	V <sub>DSM/</sub> V <sub>RSM</sub>	V <sub>DSM/</sub> V <sub>RSM</sub> +100	V
Peak Gate Current (T <sub>J</sub> = 125°C, t = 20ms)	I <sub>GM</sub>	4.0	Α
Peak Gate Power (Pulse Width $\leq$ 1.0 $\mu$ s, T <sub>C</sub> = 80°C)	P <sub>GM</sub>	20	W
Average Gate Power (T <sub>J</sub> = 125°C)	P <sub>G(AV)</sub>	1.0	W
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C
RMS Isolation Voltage (t = 300 ms, R.H. $\leq$ 30%, T <sub>A</sub> = 25°C)	V <sub>iso</sub>	2500	٧

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

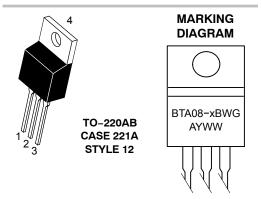
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# TRIACS 8 AMPERES RMS 600 thru 800 VOLTS





x = 6 or 8

A = Assembly Location (Optional)\*

Y = Year WW = Work Week G = Pb-Free Package

\* The Assembly Location code (A) is optional. In cases where the Assembly Location is stamped on the package the assembly code may be blank.

PIN ASSIGNMENT				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	No Connection			

### **ORDERING INFORMATION**

Device	Package	Shipping
BTA08-600BW3G	TO-220AB (Pb-Free)	50 Units / Rail
BTA08-800BW3G	TO-220AB (Pb-Free)	50 Units / Rail

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (AC) Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	2.5 63	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 seconds	TL	260	°C

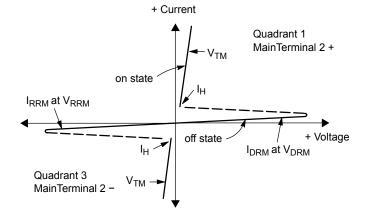
# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	1	l		I.
Peak Repetitive Blocking Current (V <sub>D</sub> = Rated V <sub>DRM</sub> , V <sub>RRM</sub> ; Gate Open)	T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	I <sub>DRM</sub> , I <sub>RRM</sub>	- -	- -	0.005 2.0	mA
ON CHARACTERISTICS						
Peak On-State Voltage (Note 2) (I <sub>TM</sub> = ±11 A Peak)		V <sub>TM</sub>	-	-	1.55	V
Gate Trigger Current (Continuous dc) ( $V_D$ = 12 V, $R_L$ = 30 $\Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		I <sub>GT</sub>	2.5 2.5 2.5	- - -	50 50 50	mA
Holding Current (V <sub>D</sub> = 12 V, Gate Open, Initiating Current = ±100 mA)		I <sub>H</sub>	-	-	60	mA
Latching Current ( $V_D$ = 12 V, $I_G$ = 60 mA) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		IL	- - -	- - -	70 90 70	mA
Gate Trigger Voltage ( $V_D$ = 12 V, $R_L$ = 30 $\Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		V <sub>GT</sub>	0.5 0.5 0.5	- - -	1.7 1.1 1.1	V
Gate Non-Trigger Voltage (T <sub>J</sub> = 125°C) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		V <sub>GD</sub>	0.2 0.2 0.2	- - -	- - -	V
DYNAMIC CHARACTERISTICS						
Rate of Change of Commutating Current, See Figure 10. (Gate Open, T <sub>J</sub> = 125°C, No Snubber)		(dl/dt) <sub>c</sub>	1.5	-	_	A/ms
Critical Rate of Rise of On–State Current $(T_J = 125^{\circ}C, f = 120 \text{ Hz}, I_G = 2 \text{ x } I_{GT}, \text{ tr} \leq 100 \text{ ns})$		dI/dt	-	-	50	A/μs
Critical Rate of Rise of Off-State Voltage (V <sub>D</sub> = 0.66 x V <sub>DRM</sub> , Exponential Waveform, Gate Open, T <sub>J</sub> = 12	25°C)	dV/dt	2000	-	_	V/μs

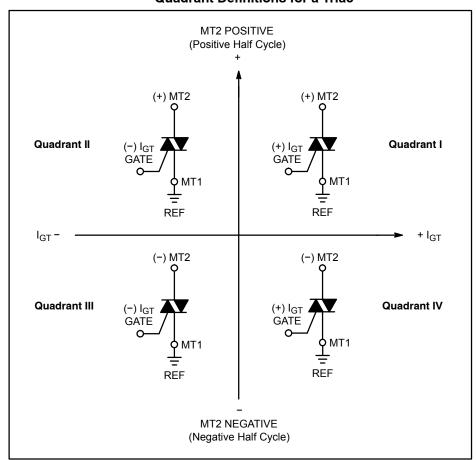
Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

# Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current

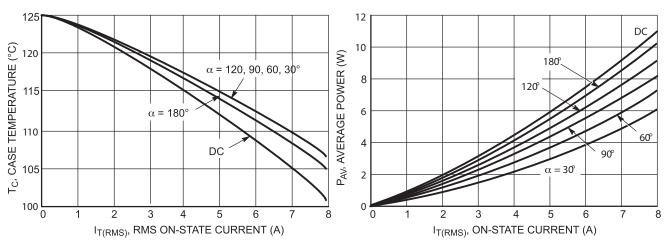


# **Quadrant Definitions for a Triac**



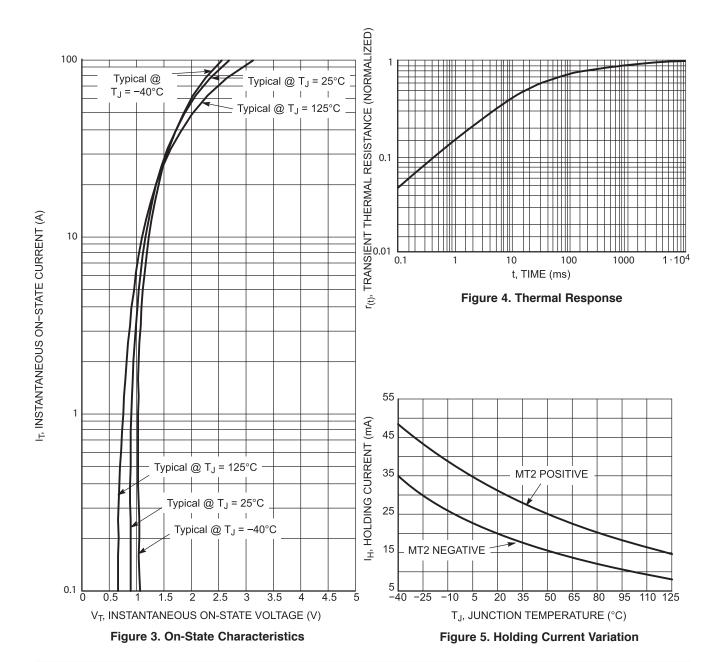
All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



**Figure 1. RMS Current Derating** 

Figure 2. On-State Power Dissipation



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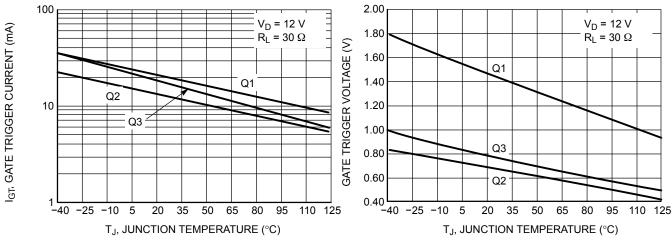


Figure 6. Gate Trigger Current Variation

Figure 7. Gate Trigger Voltage Variation

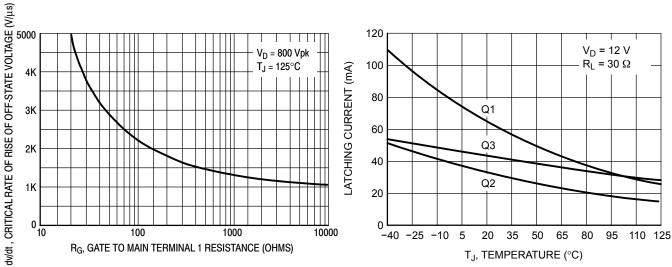


Figure 9. Critical Rate of Rise of Off-State Voltage (Exponential Waveform)

Figure 10. Latching Current Variation

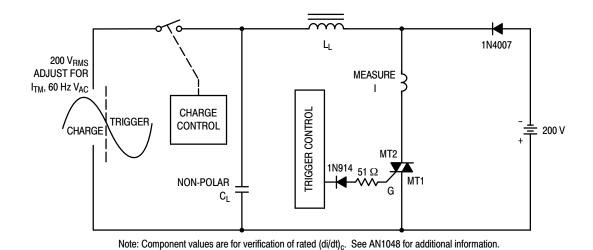
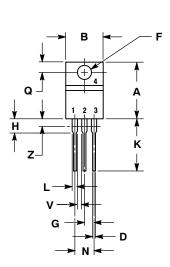
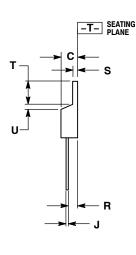


Figure 8. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)c

## PACKAGE DIMENSIONS

TO-220 CASE 221A-07 **ISSUE AA** 





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.014	0.022	0.36	0.55	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
T	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
7		0.080		2 04	

### STYLE 12:

PIN 1. MAIN TERMINAL 1

- MAIN TERMINAL 2 2.
- GATE
- NOT CONNECTED

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